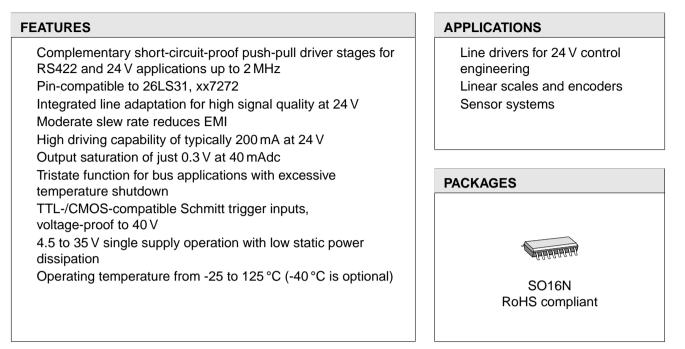
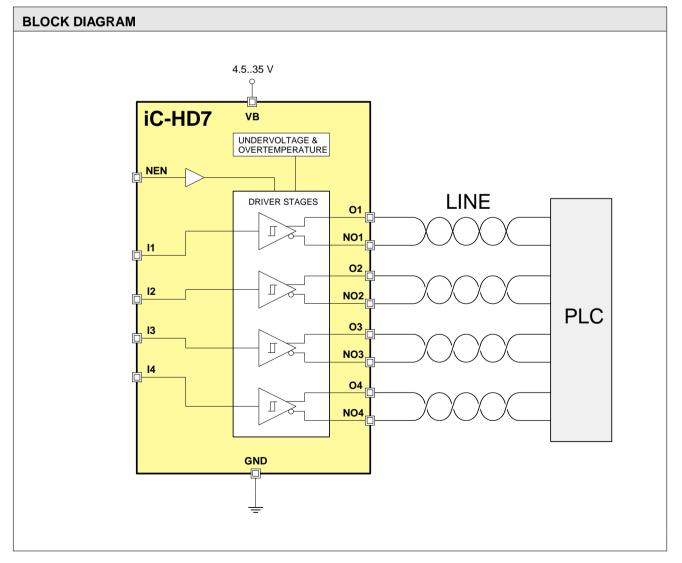


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### DESCRIPTION

iC-HD7 is a robust line driver for industrial 5 V and 24 V applications with four complementary output channels.

For signal lines with a characteristic impedance of 30 to  $140 \Omega$  the integrated line adapter, optimized to 75  $\Omega$ , minimizes ringing effects which arise when there is no line termination.

At a supply of 24 V the push-pull driver stages typically provide 200 mA to discharge the line and also have a low saturation voltage (of typically 200 mV with a 40 mA low-side load). The outputs are current limited and short-circuit-proof, shutting down with excessive temperature.

For bus applications the driver stages can be switched to high impedance by a high at input NEN.

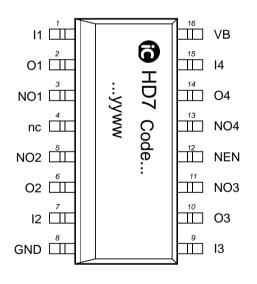
The driver stage inputs have a Schmitt trigger characteristic and are compatible with CMOS and TTL levels.

For test purposes the temperature monitor can be deactivated by applying a voltage of greater than 12 V to input NEN.

The device contains internal ESD protection circuitry.

### PACKAGES SO16N, TSSOP20

### **PIN CONFIGURATION SO16N**



#### PIN FUNCTIONS No. Name Function

1	11	Input 1

- 1 I1 Input 1 2 O1 Driver Output 1 3 NO1 Inverted Driver Output 1
- 4 nc
- 5 NO2 Inverted Driver Output 2
- 6 O2 Driver Output 2
- 7 I2 Input 2
- 8 GND Ground
- 9 13 Input 3
- 10 O3 Driver Output 3
- 11 NO3 Inverted Driver Output 3
- 12 NEN Function Input (low signal enables driver outputs)
- 13 NO4 Inverted Driver Output 4
- 14 O4 Driver Output 4
- 15 I4 Input 4
- 16 VB +4.5 to +35 V Supply Voltage



### **ABSOLUTE MAXIMUM RATINGS**

Beyond these values damage may occur; device operation is not guaranteed. Absolute Maximum Ratings are no Operating Conditions. Integrated circuits with system interfaces, e.g. via cable accessible pins (I/O pins, line drivers) are per principle endangered by injected interferences, which may compromise the function or durability. The robustness of the devices has to be verified by the user during system development with regards to applying standards and ensured where necessary by additional protective circuitry. By the manufacturer suggested protective circuitry is for information only and given without responsibility and has to be verified within the actual system with respect to actual interferences.

Item	Symbol	Parameter	Conditions			Unit
No.				Min.	Max.	
G001	VB	Supply Voltage VB		0	40	V
G002	Vin()	Voltage at Inputs I1I4		0	VB	V
G003	Vin()	Voltage at Input NEN		0	VB	V
G004	V()	Voltage at Outputs O1O4, NO1NO4		0	VB	V
G005	I()	Current in Outputs O1O4, NO1NO4		-500	500	mA
G006	Vd()	ESD Susceptibility at all pins	HBM, 100 pF discharged through 1.5 k $\Omega$		2	kV
G007	Tj	Junction Temperature		-40	150	°C
G008	Ts	Storage Temperature		-40	150	°C

### THERMAL DATA

Item	Symbol	Parameter	Conditions	[			Unit
No.				Min.	Тур.	Max.	
T01	Та	Operating Ambient Temperature (extended range to -40°C on request)		-25		125	°C
T02	Rthja	Thermal Resistance Chip To Ambient	SO16N surface mounted, no special heat sink		110		K/W



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## **ELECTRICAL CHARACTERISTICS**

ltem No.	Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Total	Device	L		U		J	1
001	VB	Permissible Supply Voltage		4.5		35	V
002	I(VB)	Supply Current in VB	NEN = lo, outputs not loaded		3.8	5.5	mA
003	I(VB)tri	Tristate Current Consumption in VB	NEN = hi		2.7		mA
004	Vc()lo	Clamp Voltage lo at NEN, Ix, NERR	I() = -1 mA	-1.2		-0.3	V
005	Vc()hi	Clamp Voltage hi at NEN, Ix, NERR	I() = 1 mA	VB + 0.3		VB + 1.2	V
006	Vc()lo	Clamp Voltage lo at O1O4, NO1NO4	VB = 0 V, I() = -10 mA	-1.2		-0.3	
007	Vc()hi	Clamp Voltage hi at O1O4, NO1NO4	VB = 0 V, I() = 10 mA	VB + 0.3		VB + 1.2	
Drive	r Outputs O	x, NOx (x = 14)					,
101	Vs()lo	Saturation Voltage lo	I() = 40 mA		0.2	0.6	V
102	Vs()hi	Saturation Voltage hi	Vs()hi = VB - V(); I() = -40 mA		0.3	0.7	V
103	lout()lo	Driving Capability lo	VB = 30 V, V() = 3 V	40	60	90	mA
104	lout()hi	Driving Capability hi	VB = 30 V, V() = VB - 3 V	-90	-60	-40	mA
105	lsc()lo	Short-Circuit Current lo	VB = 30 V, V() = VB			500	mA
106	lsc()hi	Short-Circuit Current hi	V() = 0 V	-500			mA
107	Rout()	Output Resistance	VB = 1030 V, V() = VB/2	50	75	110	Ω
108	SR()lo, hi	Slew-Rate lo/hi	VB = 24 V, CL = 100 pF		400		V/µs
109	tp()lo, hi	In/Out Propagation Delay lo/hi			75	200	ns
110	dtp()	Delay Skew	output Ox vs. NOx	-35		35	ns
111	llk()	Output Leakage Current	NEN = hi	-10		10	uA
	r Inputs Ix (x ional input vo	<b>x=14)</b> bltage range V(Ix) = 0 to 7.5 V		u			
201	Vt()lo	Threshold Voltage lo		0.8			V
202	Vt()hi	Threshold Voltage hi				2.4	V
203	Vt()hys	Input Hysteresis		0.1	0.2		V
204	I()	Input Leakage Current	0 V < V() < 4.5 V	-5		5	μA
Funct	ion Input N	EN	1				
301	Vt1()lo	Threshold Voltage lo	Driver enabled for V(NEN) < Vt1()lo	0.8			V
302	Vt1()hi	Threshold Voltage hi				2.4	V
303	Vt1()hys	Input Hysteresis		0.1	0.2		V
304	Vt2()hi	Threshold Voltage hi	Driver enabled without thermal shutdown func- tion for V(NEN) > Vt2()hi	7.5	10	12	V
305	Vt2()hys	Input Hysteresis			0.5		V
306	lin()	Input Current	5 V < V(NEN) < VB		100	400	μA
307	lin()	Input Current	0 V < V(NEN) < 5 V	-5		5	μA
Unde	rvoltage Mo	nitoring	1				
501	Voff	Undervoltage Threshold lo		3.0	3.5		V
502	Von	Undervoltage Threshold hi			3.6	4.1	V
503	Vhys	Undervoltage Hysteresis		35	100		mV
504	tp()shut	Undervoltage Lockout Delay			20		μs



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## **ELECTRICAL CHARACTERISTICS**

Operating Conditions: VB = 4.5...35 V, Tj = -40...125 °C, unless otherwise noted

Item	Symbol	Parameter	Conditions				Unit
No.				Min.	Тур.	Max.	
Temperature Monitoring							
601	Toff	Shutdown Temperature Thresh- old	NEN = Io	130	150	170	°C
602	$\Delta$ Toff	Temperature Hysteresis	NEN = Io		8		°C

## **ELECTRICAL CHARACTERISTICS: Diagrams**

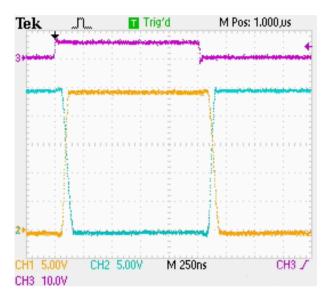


Figure 1: Example of moderate slew rate with unloadad Ox and NOx outputs (VB = 24 V)

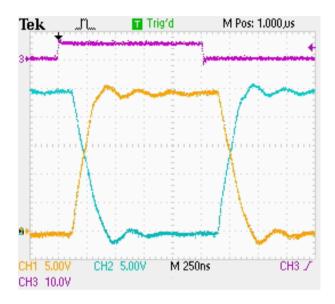


Figure 2: Example of typical line end signal without termination (VB = 24 V, length of cable 10 m)



## **APPLICATION NOTE**

### Reverse polarity and circuit protection

For reverse polarity protection electronic circuitry are usually powered via a diode D in the supply line. Under normal operating conditions, this diode will not affect function of the circuitry when the additional forward voltage drop across the diode is accounted for operating voltage specification.

If the supply voltage  $V_{supply}$  is suddenly reversed, a load capacitor C may be still fully charged. Therefore, the diode D has to be selected to withstand a voltage difference of at least twice the maximum supply voltage.

Since the reverse polarity protection diode D prevents discharging of the load capacitor C, especially at low power consumption injected charge through disturbances may in general result in capacitor voltage exceeding maximum ratings, leading to malfunction or destruction of circuitry and associated parts. Thus EMC requirements will afford more external circuitry due to the introduction of a reverse polarity diode.

Figure 3 shows the iC-HD7 with the diode D for reverse polarity protection and additional protective devices TS and ZD.

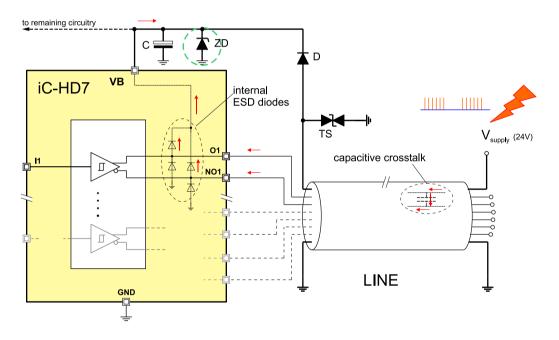


Figure 3: Circuit schematic showing protective devices D: reverse polarity protective diode; TS: bidirectional suppressor diode; ZD: supply voltage limiting zener diode

For over-voltage protection, the suppressor diode TS absorbs transients on supply line injected externally on the cable. Clamp voltage of the diode TS should be rated slightly above maximum specified supply voltage.

Due to capacitive crosstalk between the wires in the cable of the supply line, additional currents may be injected into the circuitry during transients via the driver pins of iC-HD7 connected directly to the cable. These currents can be passed to ground or to VB by the internal ESD diodes of the iC-HD7. Whereas negative current injection will simply be drained off to ground, positive current injection will charge capacitor C further to higher voltages.

By introducing an additional Zener diode ZD in parallel

to capacitor C, excessive charge can be drained off, thus limiting circuitry supply voltage to a safe value, as shown in fig. 4.

### Suggested protective devices

As stated above, diode D must withstand at least twice the maximum operating voltage. Assuming  $VB_{max}$ specified to be 30V, reverse voltage  $V_{R,D}$  of the diode D then should be at least 60 V. Current rating depends on total power consumption of the circuitry, but is usually below 1 amps. Therefore, typical 1 amps rated rectifier diodes like 1N4002 (with  $V_{R,D} = 100 \text{ V}$ ) through 1N4007 (with  $V_{R,D} = 1000 \text{ V}$ ) or equivalent types (BA157 through BA159) can be used. At VB<sub>max</sub> of 30V, neither the suppressor diode TS nor the Zener



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diode ZD should draw substantial current. Therefore, their breakdown voltage should be chosen to be some volts higher. A 36 V rated suppressor diode with 1.5kW pulse power capability like a 1N6284 or 1.5KE36 the minimum breakdown voltage measured at a test current of 1 mA is stated as 32.4 V. Also, a zener diode like a BZT03C36 rated for 36 V also shows a minimum breakdown voltage of 32.4 V, but measured at test current of 10 mA.

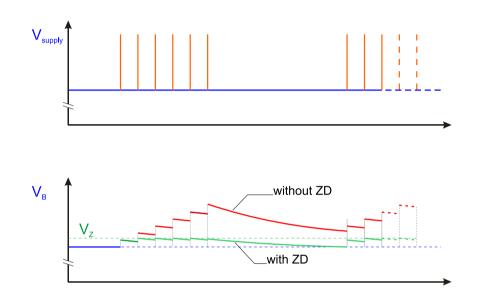


Figure 4: Using zener diode ZD to limit circuit supply voltage

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## **ORDERING INFORMATION**

Туре	Package	Order Designation
iC-HD7	SO16N	iC-HD7 SO16N

For technical support, information about prices and terms of delivery please contact:

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